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Team Nexperia

# 1 A very low V<sub>F</sub> MEGA Schottky barrier rectifiers Rev. 03 — 28 March 2007 Pro

**Product data sheet** 

### **Product profile**

### 1.1 General description

Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifiers with an integrated guard ring for stress protection, encapsulated in small Surface-Mounted Device (SMD) plastic packages.

Table 1. **Product overview** 

| Type number | Package |       | Configuration |
|-------------|---------|-------|---------------|
|             | NXP     | JEITA |               |
| PMEG2010AEH | SOD123F | -     | single        |
| PMEG2010AET | SOT23   | -     | single        |

#### 1.2 Features

Forward current: I<sub>F</sub> ≤ 1 A

Reverse voltage: V<sub>R</sub> ≤ 20 V

Very low forward voltage

Small SMD plastic packages

#### 1.3 Applications

- Low voltage rectification
- High efficiency DC-to-DC conversion
- Switch mode power supply
- Reverse polarity protection
- Low power consumption applications

#### 1.4 Quick reference data

Table 2. **Quick reference data** 

| Symbol         | Parameter       | Conditions                 | Min          | Тур | Max | Unit |
|----------------|-----------------|----------------------------|--------------|-----|-----|------|
| I <sub>F</sub> | forward current | $T_{sp} \le 55  ^{\circ}C$ | -            | -   | 1   | Α    |
| $V_R$          | reverse voltage |                            | -            | -   | 20  | V    |
| $V_{F}$        | forward voltage | I <sub>F</sub> = 1 A       | <u>[1]</u> _ | 380 | 430 | mV   |

[1] Pulse test:  $t_p \le 300 \ \mu s$ ;  $\delta \le 0.02$ .



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### 2. Pinning information

Table 3. Pinning

| Table 3. | Filling       |                    |        |
|----------|---------------|--------------------|--------|
| Pin      | Description   | Simplified outline | Symbol |
| SOD123F  |               |                    |        |
| 1        | cathode       | [1]                | . 54   |
| 2        | anode         | 1 2                | 1 🔀 2  |
|          |               |                    | sym001 |
| SOT23    |               |                    |        |
| 1        | anode         |                    | _      |
| 2        | not connected | 3                  | 3      |
| 3        | cathode       | 1 2                | 1      |

<sup>[1]</sup> The marking bar indicates the cathode.

### 3. Ordering information

Table 4. Ordering information

| Type number | Package |  |         |
|-------------|---------|--|---------|
|             | Name    | Description                              | Version |
| PMEG2010AEH | -       | plastic surface-mounted package; 2 leads | SOD123F |
| PMEG2010AET | -       | plastic surface-mounted package; 3 leads | SOT23   |

### 4. Marking

Table 5. Marking codes

| Type number | Marking code <sup>[1]</sup> |
|-------------|-----------------------------|
| PMEG2010AEH | AF                          |
| PMEG2010AET | *AX                         |

[1] \* = -: made in Hong Kong

\* = p: made in Hong Kong

\* = t: made in Malaysia

\* = W: made in China

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### 5. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol           | Parameter                           | Conditions  | Min          | Max  | Unit |
|------------------|-------------------------------------|---|--------------|------|------|
| $V_{R}$          | reverse voltage                     |   | -            | 20   | V    |
| l <sub>F</sub>   | forward current                     | T <sub>sp</sub> ≤ 55 °C   | -            | 1    | Α    |
| I <sub>FRM</sub> | repetitive peak forward current     | $\begin{array}{l} t_p \leq 1 \text{ ms;} \\ \delta \leq 0.25 \end{array}$ |              |      |      |
|                  | PMEG2010AEH                         |   | -            | 7    | Α    |
|                  | PMEG2010AET                         |   | -            | 6    | Α    |
| I <sub>FSM</sub> | non-repetitive peak forward current | square wave;<br>t <sub>p</sub> = 8 ms                                     | -            | 9    | Α    |
| P <sub>tot</sub> | total power dissipation             | T <sub>amb</sub> ≤ 25 °C  |              |      |      |
|                  | PMEG2010AEH                         |   | <u>[1]</u> _ | 375  | mW   |
|                  |                                     |   | [2] _        | 830  | mW   |
|                  | PMEG2010AET                         |   | [1] -        | 280  | mW   |
|                  |                                     |   | [2] _        | 420  | mW   |
| T <sub>j</sub>   | junction temperature                |   | -            | 150  | °C   |
| T <sub>amb</sub> | ambient temperature                 |   | -65          | +150 | °C   |
| T <sub>stg</sub> | storage temperature                 |   | -65          | +150 | °C   |

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

### 6. Thermal characteristics

Table 7. Thermal characteristics

| Symbol         | Parameter  | Conditions  | Min        | Тур | Max | Unit |
|----------------|--|-------------|------------|-----|-----|------|
| $R_{th(j-a)}$  | thermal resistance from junction to ambient      | in free air | <u>[1]</u> |     |     |      |
|                | PMEG2010AEH                                      |             | [2] -      | -   | 330 | K/W  |
|                |  |             | [3] _      | -   | 150 | K/W  |
|                | PMEG2010AET                                      |             | [2] -      | -   | 440 | K/W  |
|                |  |             | [3] _      | -   | 300 | K/W  |
| $R_{th(j-sp)}$ | thermal resistance from junction to solder point |             | <u>[4]</u> |     |     |      |
|                | PMEG2010AEH                                      |             | -          | -   | 60  | K/W  |
|                | PMEG2010AET                                      |             | -          | -   | 120 | K/W  |

<sup>[1]</sup> For Schottky barrier diodes thermal runaway has to be considered, as in some applications the reverse power losses P<sub>B</sub> are a significant part of the total power losses.

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<sup>[2]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm<sup>2</sup>.

<sup>[2]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

<sup>[3]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm<sup>2</sup>.

<sup>[4]</sup> Soldering point of cathode tab.

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### 7. Characteristics

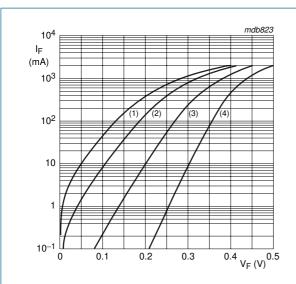
Table 8. Characteristics

T<sub>amb</sub> = 25 °C unless otherwise specified.

| amo                            |                       | '                         |            |     |     |      |
|--------------------------------|-----------------------|---------------------------|------------|-----|-----|------|
| Symbol                         | Parameter             | Conditions                | Min        | Тур | Max | Unit |
| V <sub>F</sub> forward voltage | forward voltage       |                           | <u>[1]</u> |     |     |      |
|                                |                       | I <sub>F</sub> = 10 mA    | -          | 200 | 220 | mV   |
|                                |                       | $I_F = 100 \text{ mA}$    | -          | 265 | 290 | mV   |
|                                |                       | I <sub>F</sub> = 1 A      | -          | 380 | 430 | mV   |
| I <sub>R</sub>                 | reverse current       | $V_R = 5 V$               | -          | 15  | 50  | μΑ   |
|                                | V <sub>R</sub> = 10 V | -                         | 20         | 80  | μΑ  |      |
|                                |                       | V <sub>R</sub> = 20 V     | -          | 50  | 200 | μΑ   |
| C <sub>d</sub>                 | diode capacitance     | $V_R = 5 V$ ; $f = 1 MHz$ | -          | 55  | 70  | pF   |
|                                |                       |                           |            |     |     |      |

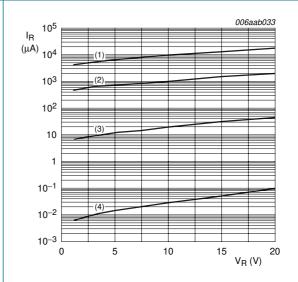
<sup>[1]</sup> Pulse test:  $t_p \le 300~\mu s;~\delta \le 0.02.$ 

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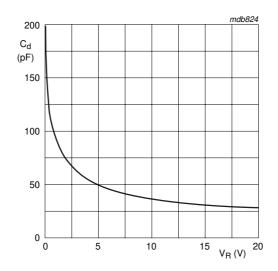
- (1)  $T_{amb} = 125 \, ^{\circ}C$
- (2)  $T_{amb} = 85 \, ^{\circ}C$
- (3)  $T_{amb} = 25 \, ^{\circ}C$
- (4)  $T_{amb} = -40 \, ^{\circ}C$

Fig 1. Forward current as a function of forward voltage; typical values



- (1)  $T_{amb} = 125 \, ^{\circ}C$
- (2)  $T_{amb} = 85 \, ^{\circ}C$
- (3)  $T_{amb} = 25 \, ^{\circ}C$
- (4)  $T_{amb} = -40 \, ^{\circ}C$

Fig 2. Reverse current as a function of reverse voltage; typical values

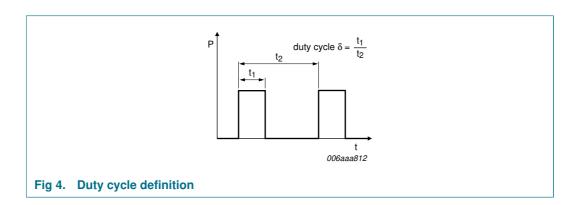


f = 1 MHz; T<sub>amb</sub> = 25 °C

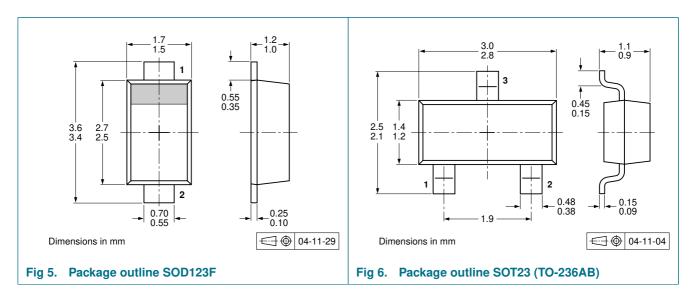
Fig 3. Diode capacitance as a function of reverse voltage; typical values

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### 8. Test information



### 9. Package outline



### 10. Packing information

Table 9. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

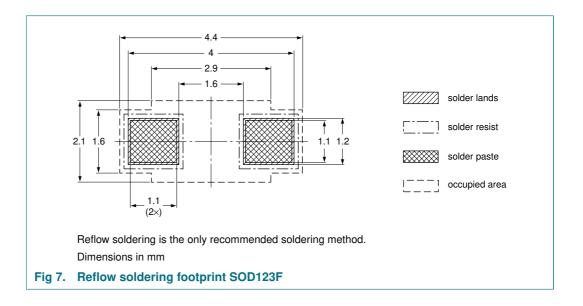
| Type number | Package | Description                    | Packing o | <b>Juantity</b> |
|-------------|---------|--------------------------------|-----------|-----------------|
|             |         |                                | 3000      | 10000           |
| PMEG2010AEH | SOD123F | 4 mm pitch, 8 mm tape and reel | -115      | -135            |
| PMEG2010AET | SOT23   | 4 mm pitch, 8 mm tape and reel | -215      | -235            |

[1] For further information and the availability of packing methods, see Section 14.

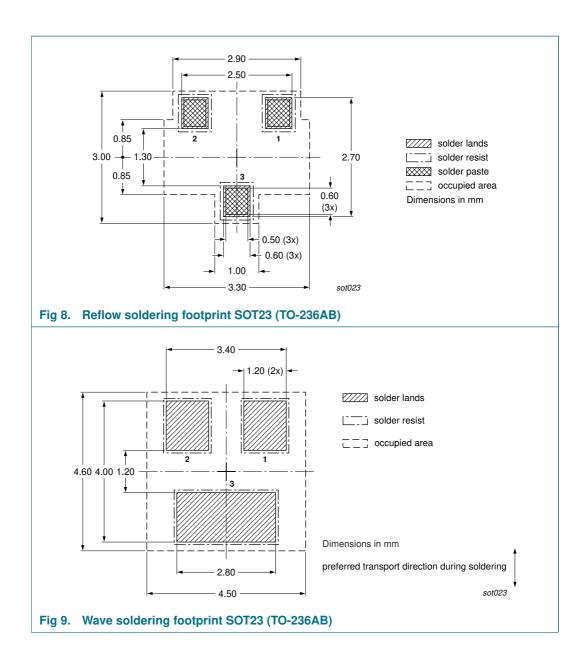
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### 11. Soldering



### 1 A very low V<sub>F</sub> MEGA Schottky barrier rectifiers



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### 12. Revision history

### Table 10. Revision history

| Document ID               | Release date                      | Data sheet status                      | Change notice        | Supersedes         |
|---------------------------|-----------------------------------|--|----------------------|--------------------|
| PMEG2010AEH_PMEG2010AET_3 | 20070328                          | Product data sheet                     | -                    | PMEG2010AEH_2      |
| Modifications:            |                                   | f this data sheet has bee              | •                    | ply with the new   |
|                           | <ul> <li>Legal texts h</li> </ul> | ave been adapted to the                | new company name     | where appropriate. |
|                           | <ul> <li>Type number</li> </ul>   | PMEG2010AET added                      |                      |                    |
|                           | • Section 1.1 "                   | General description": am               | ended                |                    |
|                           | • Table 1 "Proc                   | duct overview": added                  |                      |                    |
|                           | • Table 7 "The                    | rmal characteristics": Tat             | ole note 1 amended   |                    |
|                           | • Table 7 "The                    | rmal characteristics": Tal             | ole note 4 added     |                    |
|                           | • Table 8 "Cha                    | racteristics": C <sub>d</sub> diode ca | pacitance conditions | adapted            |
|                           | • Figure 2: am                    | ended                                  |                      |                    |
|                           | Section 8 "Te                     | est information": added                |                      |                    |
|                           | Section 13 "L                     | <u>egal information"</u> : updat       | ed                   |                    |
| PMEG2010AEH_2             | 20050526                          | Product data sheet                     | -                    | PMEG2010AEH_1      |
| PMEG2010AEH_1             | 20050406                          | Product data sheet                     | -                    | -                  |

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### 13. Legal information

#### 13.1 Data sheet status

| Document status[1][2]          | Product status[3] | Definition  |
|--------------------------------|-------------------|---|
| Objective [short] data sheet   | Development       | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification     | This document contains data from the preliminary specification.                       |
| Product [short] data sheet     | Production        | This document contains the product specification.                                     |

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <a href="http://www.nxp.com">http://www.nxp.com</a>.

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### **NXP Semiconductors**

# PMEG2010AEH; PMEG2010AET

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